

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)
YOR919990281US3 (12795AB)

Application Number **10/691,299**
Unassigned

Applicant(s)
Paul D. Agnello, et al.

Filing Date
Herewith

Group Art Unit **2814**
Unassigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
mbh		5,510,295	4/23/96	Cabral, Jr., et al.	148	026.147	
mbh		5,608,226	3/4/97	Yamada, et al.	250	492.2	
mbh		5,624,869	4/29/97	Agnello, et al.	257	E21.165	
mbh		5,828,131	10/27/98	Cabral, Jr., et al.	257	768	

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

mbh	M. Lawrence, et al., (1991), "Growth of Epitaxial CoSi2 on (100)Si," Appl. Phys. Lett., Vol. 58, No. 12, pp. 1308-1310
mbh	C. Cabral, Jr., et al., (1995), "In-Situ X Ray Diffraction and Resistivity Analysis of CoSi2 Phase Formation With and Without a Ti Interlayer at Rapid Thermal Annealing Rates," Mat. Res. Soc. Symp. Proc., Vol. 375, pp. 253-258.

EXAMINER **Murleen Bin Hoff** DATE CONSIDERED **11/23/95**

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.